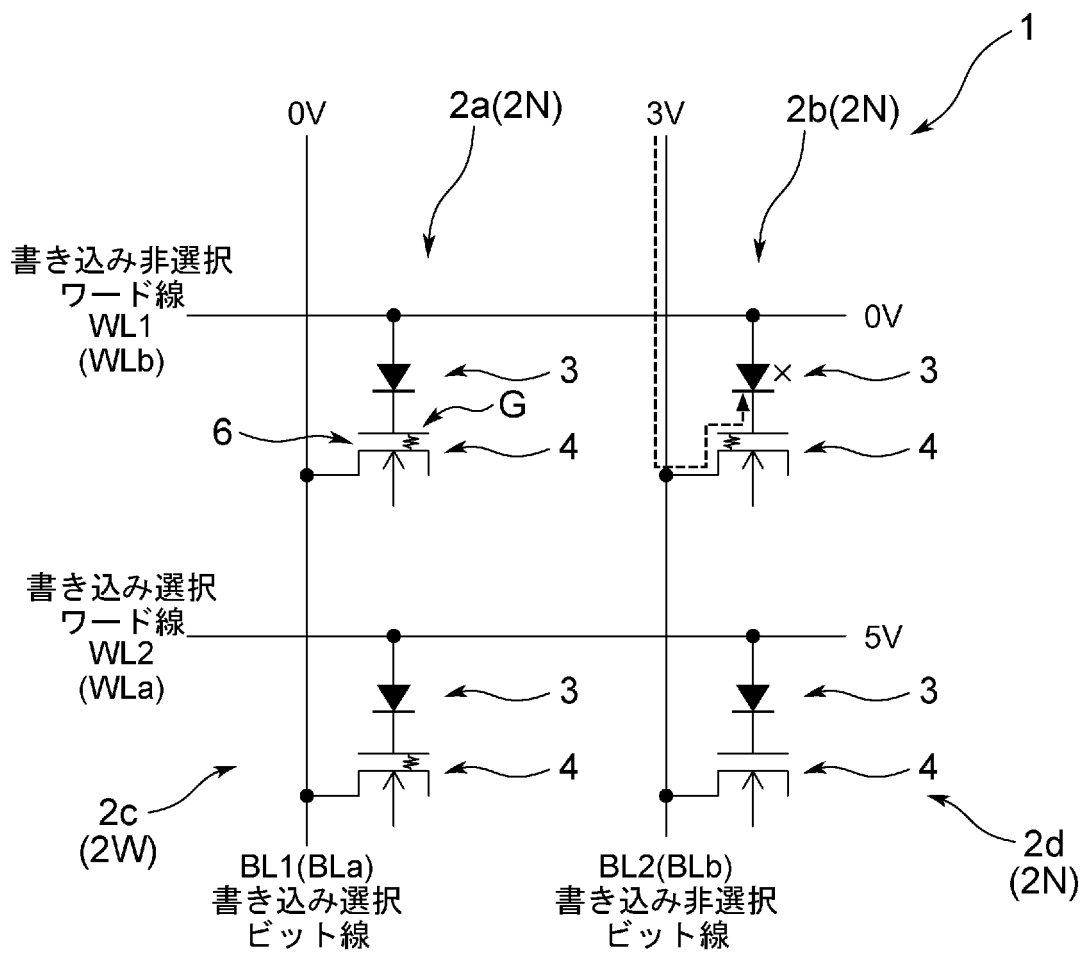
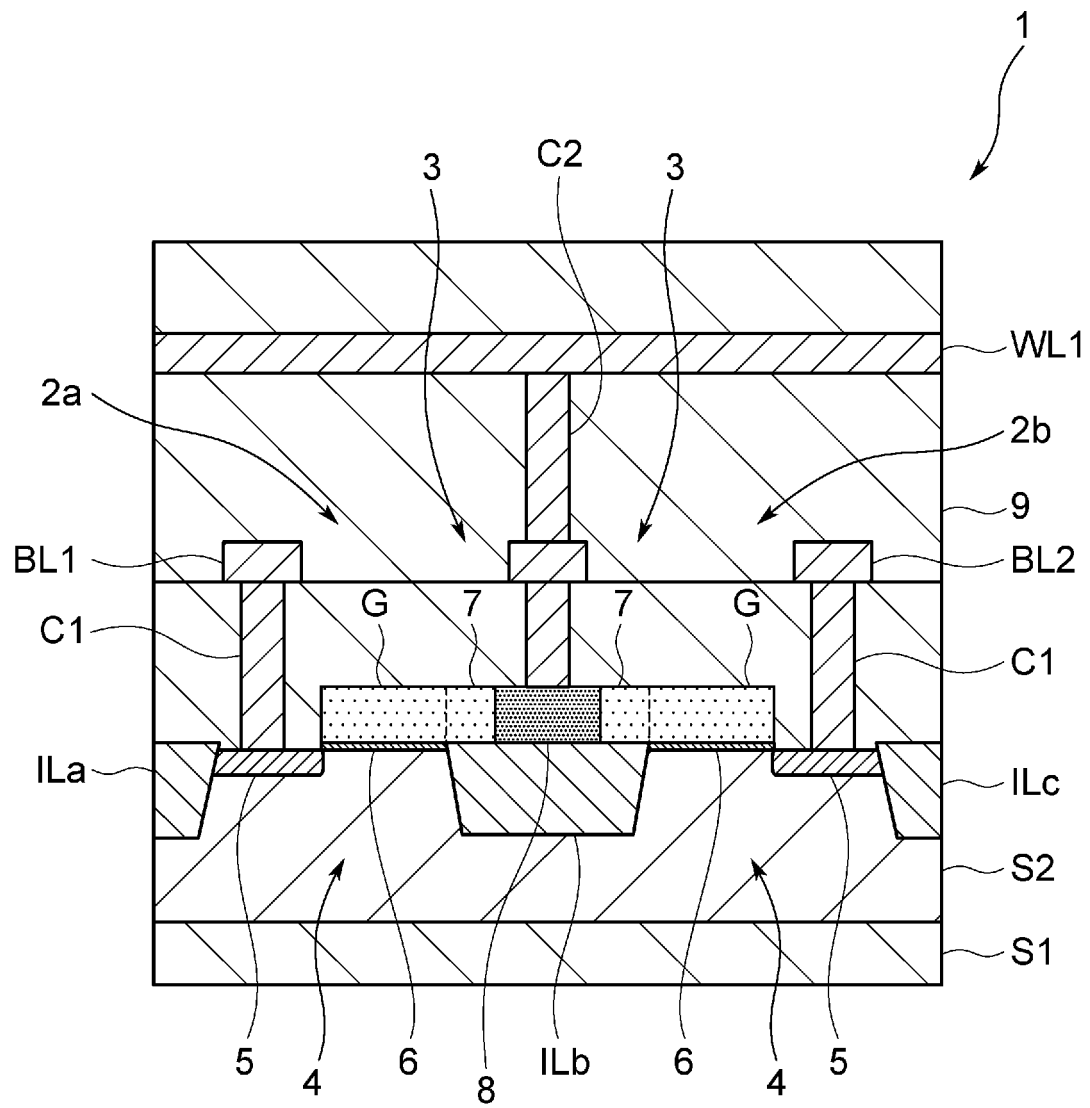
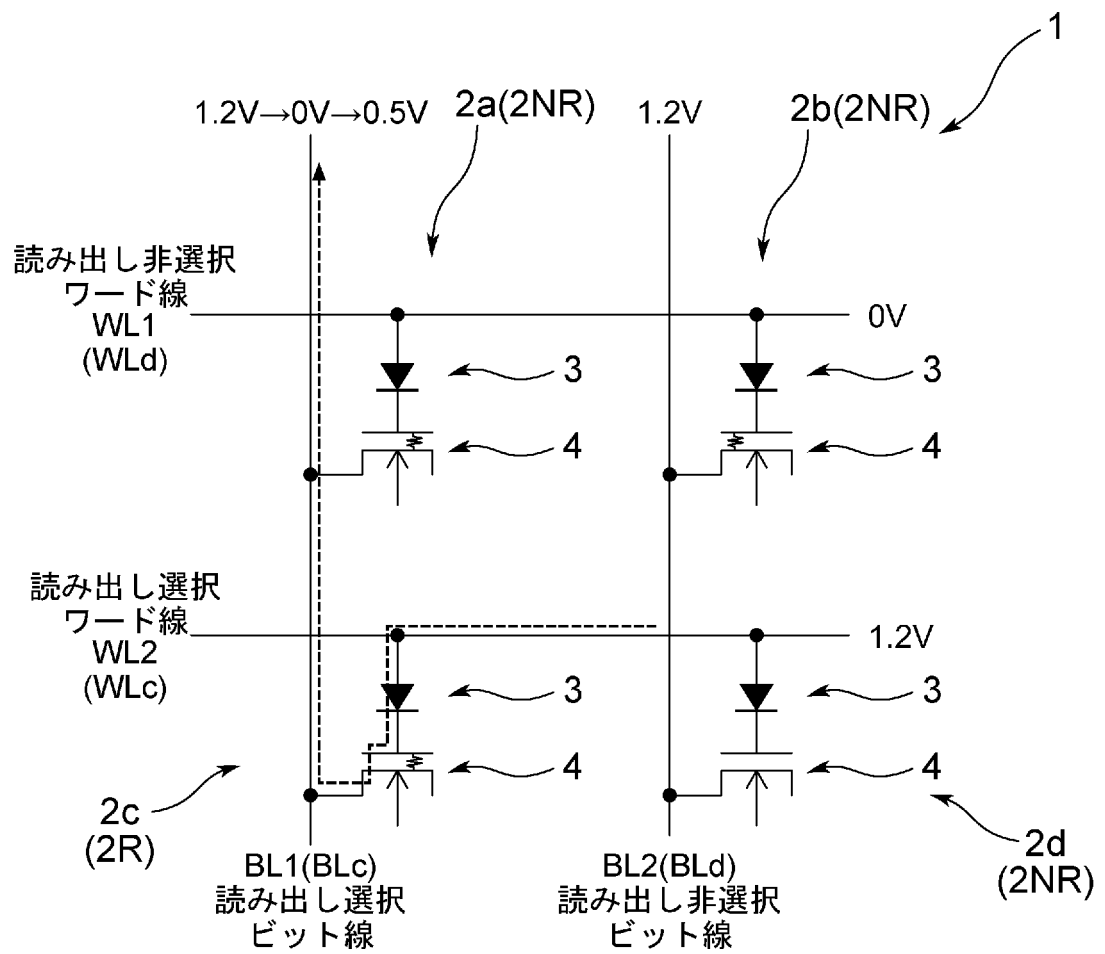




[図2]



[図3]



[図4]

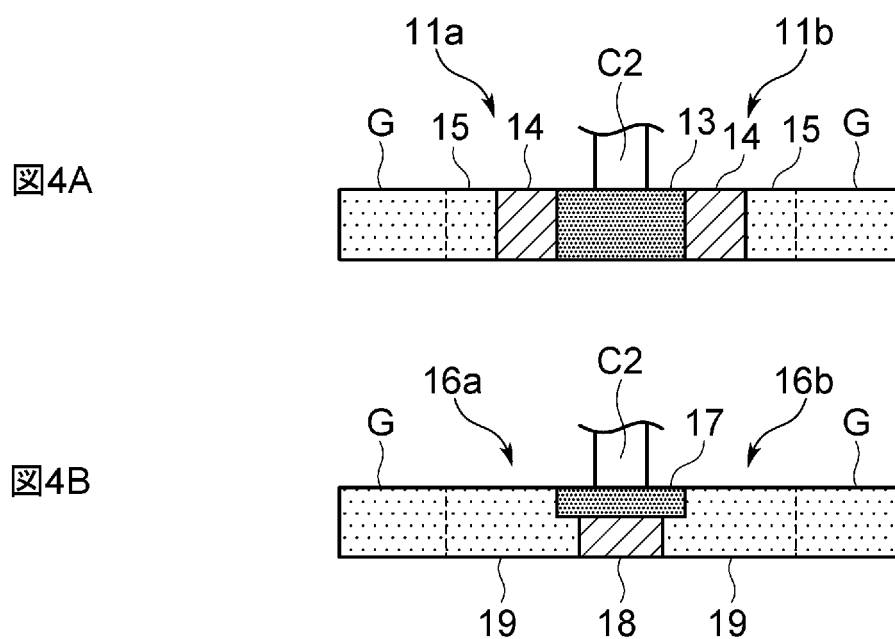
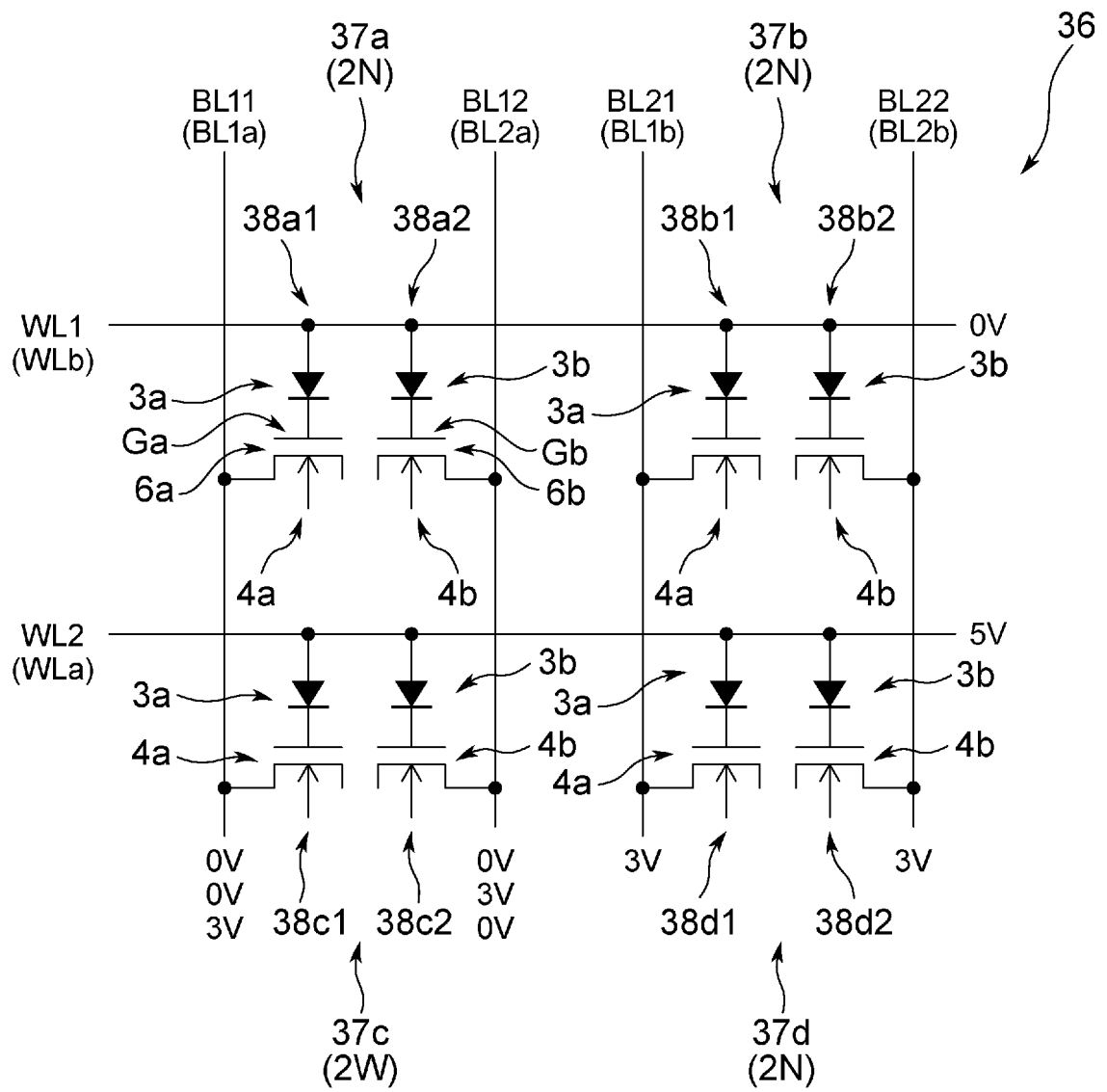


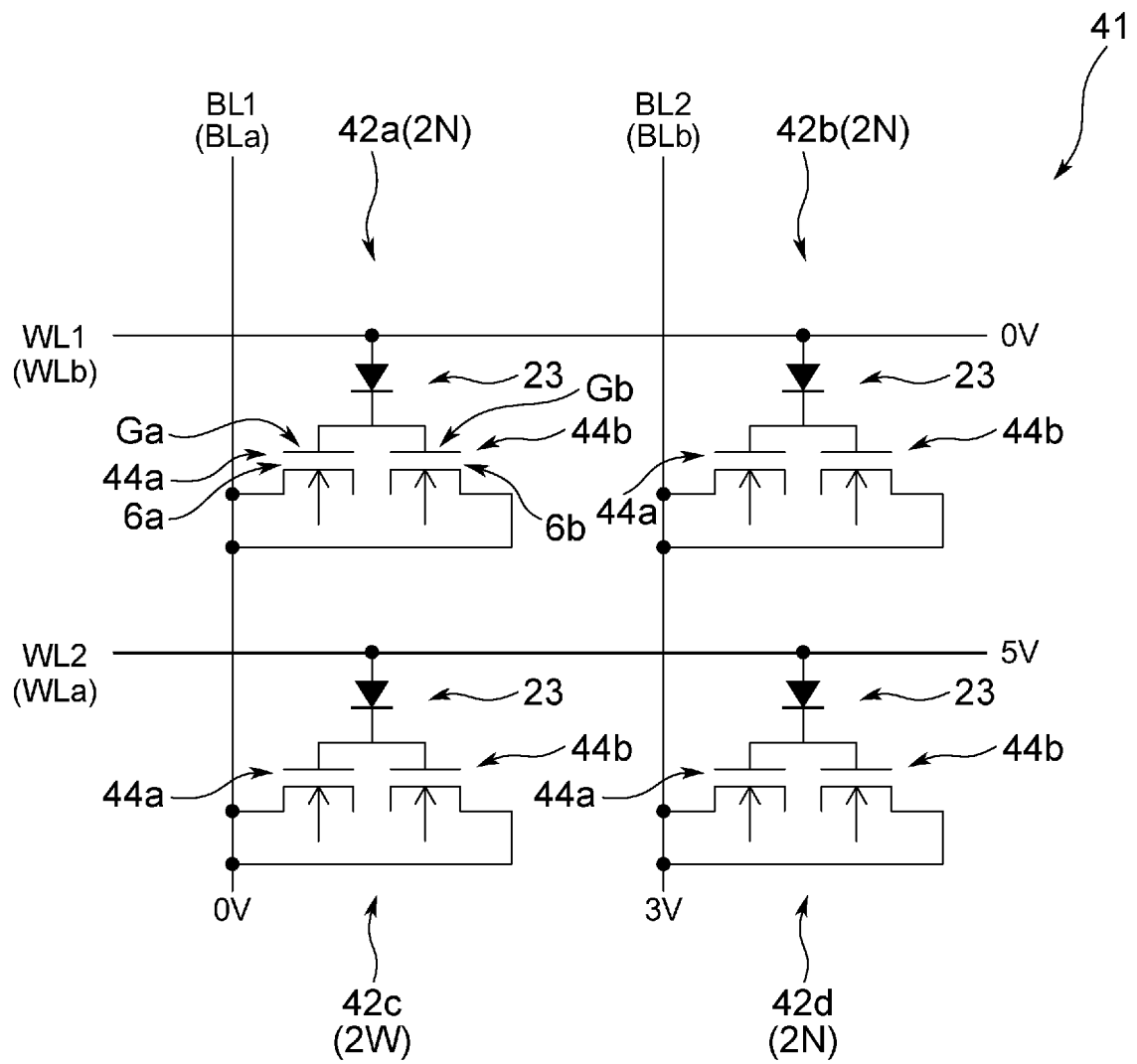
FIG. 6A is a cross-sectional view of a semiconductor device. It shows a substrate with a central region 23 containing a structure 28. A layer 29 is on top of 28, and a layer C2 is on top of 29. The substrate is labeled Ga on the left and Gb on the right. An arrow points to the central region 23.

Figure 6B is a cross-sectional view of a device. It shows a substrate 30 with a layer 32 on top. A structure C2 is formed on layer 32. The substrate 30 is divided into regions Ga and Gb by a vertical line. A layer 33 is located beneath the substrate 30.

[図7]



[図8]



[図9]

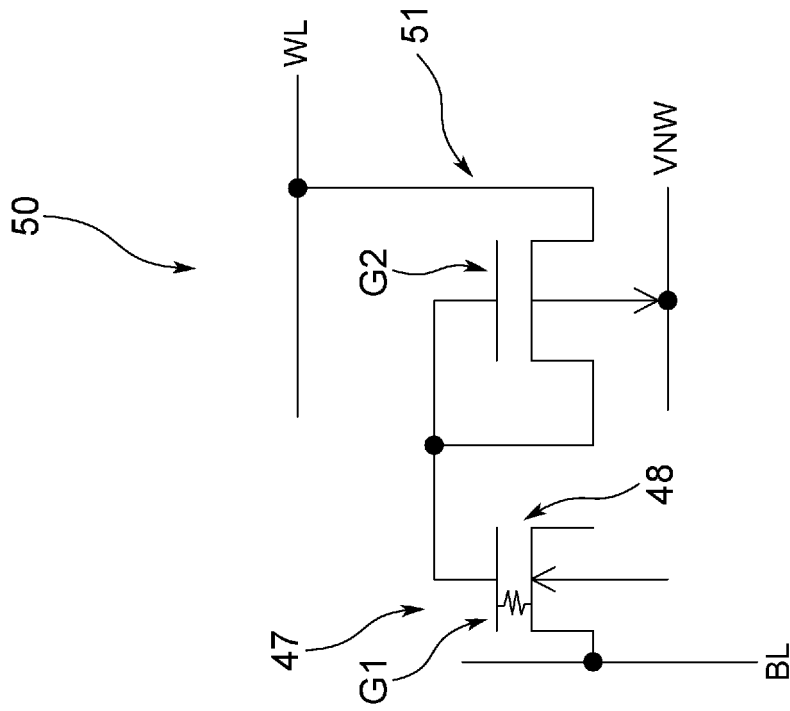


図9B

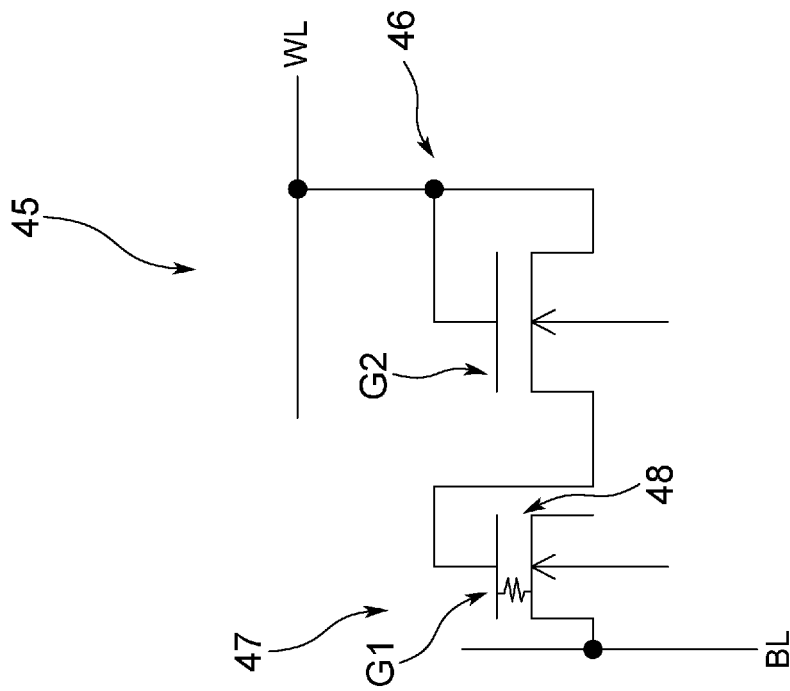
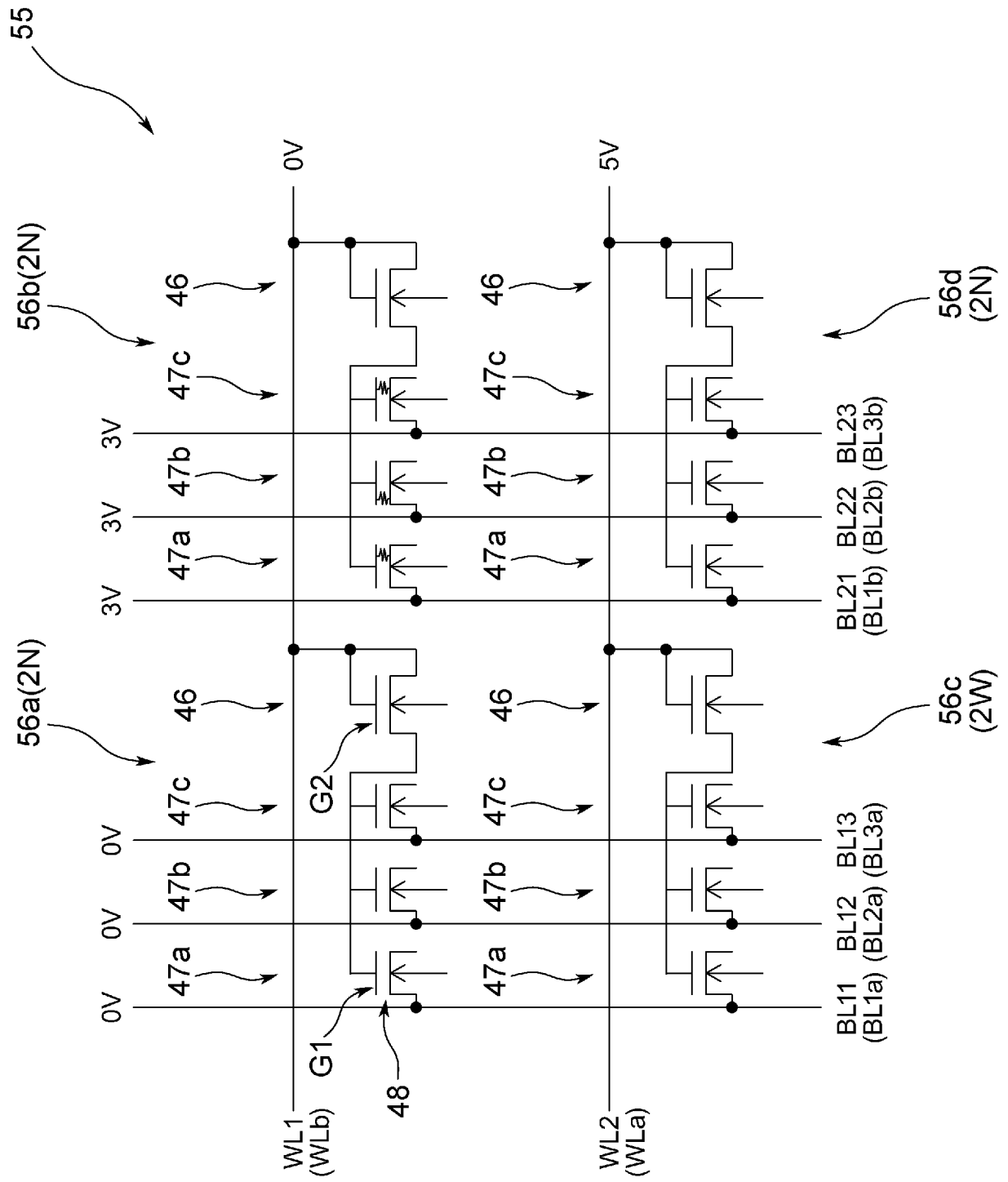


図9A

[図10]



[図11]

